

Product Change Notification

Change Title	DDR4 product change notice from 2400 Samsung 512x8 E die IC to 2666 Samsung 512x8 F die IC	Date	2020/02/27	PCN No	20022701
PCN level:	Major				
Models :	Innodisk DDR4 Samsung 512x8 E die IC DRAM Module products				
Category:	Hardware - IC				

Key Characteristics of the Change:

Due to supply condition, Innodisk hereby to announce the product change plan for all of DDR4 2400 Samsung 512x8 E die IC assembled modules

Description:

Innodisk is going to process DDR4 2400 Samsung 512x8 E die IC product termination and running change to DDR4 2666 Samsung 512x8 F die IC product series.

Include below products: DDR4 2400/2133 512x8 4GB/8GB DRAM Modules

Key Milestone Dates

Last Purchase Date: 2020/05/31

Last Shipment Date: 2020/08/31

*Milestone dates are subject to change based on business and operational conditions.

Affected Model Table

Current Part Number	New Part Number
M4DS-4GSSPC0J-E	M4DI-4GSSPCSJ-F
M4DS-4GSSIC0J-E	M4DI-4GSSICSJ-F
M4DS-4GSSP50J-E	M4DI-4GSSICSJ-F
M4CS-4GSSLC0J-E	M4CI-4GSSLC SJ-F
M4CS-4GSSSC0J-E	M4CI-4GSSSC SJ-F
M4CS-4GSSL50J-E	M4CI-4GSSSC SJ-F
M4MS-4GSSXC0J-E	M4MI-4GSSXCSJ-F
M4MS-4GSS5C0J-E	M4MI-4GSS5CSJ-F
M4RS-4GSSAC0J-E	M4RI-4GSSACSJ-F
M4RS-4GSSCC0J-E	M4RI-4GSSCC SJ-F
M4RS-4GSSC50J-E	M4RI-4GSSC5SJ-F
M4RS-4GSSA50J-E	M4RI-4GSSA5SJ-F
M4SS-4GSSNC0J-E	M4SI-4GSSNCSJ-F
M4SS-4GSS3C0J-E	M4SI-4GSS3CSJ-F
M4SS-4GSSN50J-E	M4SI-4GSSN5SJ-F
M4US-4GSSJC0J-E	M4UI-4GSSJCSJ-F
M4US-4GSSVC0J-E	M4UI-4GSSVCSJ-F
M4US-4GSSJ50J-E	M4UI-4GSSJ5SJ-F
M4DS-8GSSQC0J-E	M4DI-8GSSQCSJ-F
M4DS-8GSSQ50J-E	M4DI-8GSSQ5SJ-F
M4CS-8GSSMC0J-E	M4CI-8GSSMCSJ-F
M4CS-8GSSTC0J-E	M4CI-8GSSTCSJ-F
M4CS-8GSSM50J-E	M4CI-8GSSM5SJ-F
M4MS-8GSSYC0J-E	M4MI-8GSSYCSJ-F
M4RS-8GSSBC0J-E	M4RI-8GSSBCSJ-F
M4RS-8GSSDC0J-E	M4RI-8GSSDCSJ-F
M4RS-8GSSD50J-E	M4RI-8GSSD5SJ-F
M4RS-8GSSB50J-E	M4RI-8GSSB5SJ-F
M4SS-8GSSOC0J-E	M4SI-8GSSOCSJ-F
M4SS-8GSSO50J-E	M4SI-8GSSO5SJ-F
M4US-8GSSKC0J-E	M4UI-8GSSKCSJ-F
M4US-8GSSWC0J-E	M4UI-8GSSWCSJ-F
M4US-8GSSW50J-E	M4UI-8GSSW5SJ-F
M4US-8GSSK50J-E	M4UI-8GSSK5SJ-F
M4XS-8GSSQC0J-E	M4XI-8GSSQCSJ-F
M4SS-4GSSNCRG-E	M4SI-4GSSNCRG-F
M4US-4GSSJCRG-E	M4UI-4GSSJCRG-F
M4DS-4GSSPCRG-E	M4DI-4GSSPCRG-F
M4CS-4GSSLCRG-E	M4CI-4GSSLCRG-F
M4RS-4GSSACRG-E	M4RI-4GSSACRG-F

M4SS-4GSSN5RG-E	M4SI-4GSSN5RG-F
M4US-4GSSJ5RG-E	M4UI-4GSSJ5RG-F
M4DS-4GSSP5RG-E	M4DI-4GSSP5RG-F
M4CS-4GSSL5RG-E	M4CI-4GSSL5RG-F
M4RS-4GSSA5RG-E	M4RI-4GSSA5RG-F
M4RS-4GSSC5RG-E	M4RI-4GSSC5RG-F
M4US-4GSSVCRG-E	M4UI-4GSSVCRG-F
M4CS-4GSSSCRG-E	M4CI-4GSSSCRG-F
M4SS-4GSS3CRG-E	M4SI-4GSS3CRG-F
M4DS-4GSSICRG-E	M4DI-4GSSICRG-F
M4RS-4GSSCCRG-E	M4RI-4GSSCCRG-F
M4SS-8GSSOCRG-E	M4SI-8GSSOCRG-F
M4US-8GSSKCRG-E	M4UI-8GSSKCRG-F
M4DS-8GSSQCRG-E	M4DI-8GSSQCRG-F
M4CS-8GSSMCRG-E	M4CI-8GSSMCRG-F
M4RS-8GSSDCRG-E	M4RI-8GSSBCRG-F
M4SS-8GSSO5RG-E	M4SI-8GSSO5RG-F
M4US-8GSSK5RG-E	M4UI-8GSSK5RG-F
M4DS-8GSSQ5RG-E	M4DI-8GSSQ5RG-F
M4CS-8GSSM5RG-E	M4CI-8GSSM5RG-F
M4RS-8GSSB5RG-E	M4RI-8GSSB5RG-F
M4RS-8GSSD5RG-E	M4RI-8GSSD5RG-F
M4US-8GSSWCRG-E	M4UI-8GSSWCRG-F
M4CS-8GSSTCRG-E	M4CI-8GSSTCRG-F
M4RS-8GSSDCRG-E	M4RI-8GSSDCRG-F

Innodisk will reserve the right to process DDR4 product change all M4xS-xGSSxxx-E to M4xI-xGSSxxx-F and if the PN is not list on above table

Notes:

- (1) For the replacement samples, **DDR4 2666 Samsung 512x8 F die IC** assembled solutions, are currently available.
- (2) No response from customers will be deemed as acceptance of the change and the change will be implemented pursuant to the key milestones. Innodisk apologizes for any inconvenience caused by this and appreciate your understanding.
- (3) Innodisk promises that new items deliver quality and reliability are JEDEC compliant. If there is any further inquiry of our products or product specification, please contact your Innodisk contact sales person for support

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